

VS-MURB820PbF, VS-MURB820-1PbF

Vishay Semiconductors

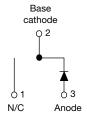
Ultrafast Rectifier, 8 A FRED Pt®

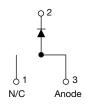




TO-263AB (D²PAK)

TO-262AA





VS-MURB820PbF

VS-MURB820-1PbF

PRODUCT SUMMARY	
Package	TO-263AB (D ² PAK), TO-262AA
I _{F(AV)}	8 A
V_{R}	200 V
V _F at I _F	0.895 V
t _{rr}	35 ns
T _J max.	175 °C
Diode variation	Single die

FEATURES

- Ultrafast recovery time
- · Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



· Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS COMPLIANT **HALOGEN** FREE

DESCRIPTION / APPLICATIONS

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Peak repetitive reverse voltage	V_{RRM}		200	V	
Average rectified forward current	I _{F(AV)}	Total device, rated V _R , T _C = 150 °C	8		
Non-repetitive peak surge current	I _{FSM}		100	Α	
Peak repetitive forward current	I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 150 °C	16		
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	200	-	-	
Forward voltage	V _F	I _F = 8 A	-	-	0.975	V
Forward voitage	٧F	I _F = 8 A, T _J = 150 °C	-	-	0.895	
Devene leekene euwent		$V_R = V_R$ rated	-	-	5	
Reverse leakage current I _R	I _R	T _J = 150 °C, V _R = V _R rated	-	-	250	μΑ
Junction capacitance	C _T	V _R = 200 V	-	25	-	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 A$, $dI_F/dt =$	$50 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 30 \text{ V}$	1	ı	35	
Reverse recovery time	t _{rr}	I _F = 0.5 A, I _R = 1.0 A, I _{REC} = 0.25 A		-	-	25	
neverse recovery time		T _J = 25 °C	I _F = 8 A dI _F /dt = 200 A/μs V _R = 160 V	-	20	-	ns
		T _J = 125 °C		-	34	-	
Dools recovery assured	I _{RRM}	T _J = 25 °C		-	1.7	-	۸
Peak recovery current		T _J = 125 °C		-	4.2	-	Α
Poverse recovery charge	Q _{rr}	T _J = 25 °C		-	23	-	nC
Reverse recovery charge		T _J = 125 °C		-	75	-	IIC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case	R _{thJC}		-	-	3.0	
Thermal resistance, junction to ambient	R _{thJA}		-	-	50	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Woight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-263AB (D ² PAK)		MUF	RB820	
iviarking device		Case style TO-262AA		MURB820-1		

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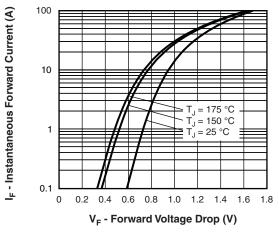


Fig. 1 - Typical Forward Voltage Drop Characteristics

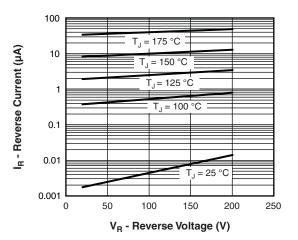


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

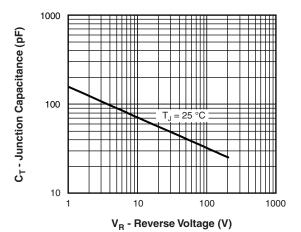


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

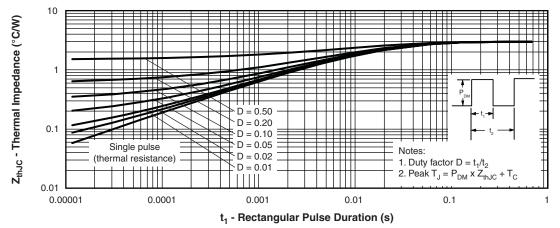


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

50

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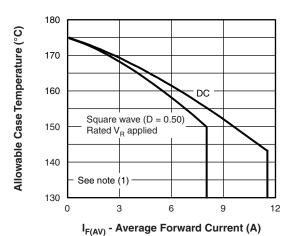


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

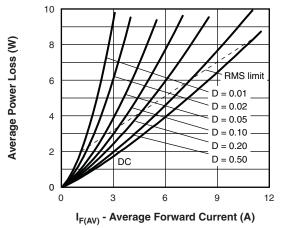


Fig. 6 - Forward Power Loss Characteristics

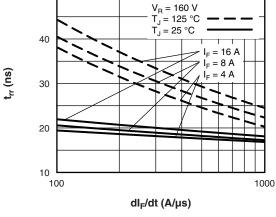


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

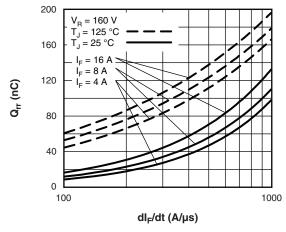


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = Inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = Rated V_R

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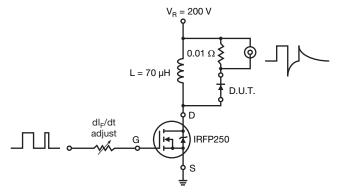
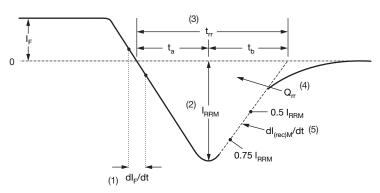


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

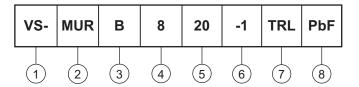
Fig. 10 - Reverse Recovery Waveform and Definitions

VS-MURB820PbF, VS-MURB820-1PbF

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Ultrafast MUR series

Current rating (8 = 8 A)

- Voltage rating (20 = 200 V)

None = D²PAK

• -1 = TO-262

7 - • None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D²PAK package)

• TRR = tape and reel (right oriented, for D²PAK package)

8 - PbF = lead (Pb)-free

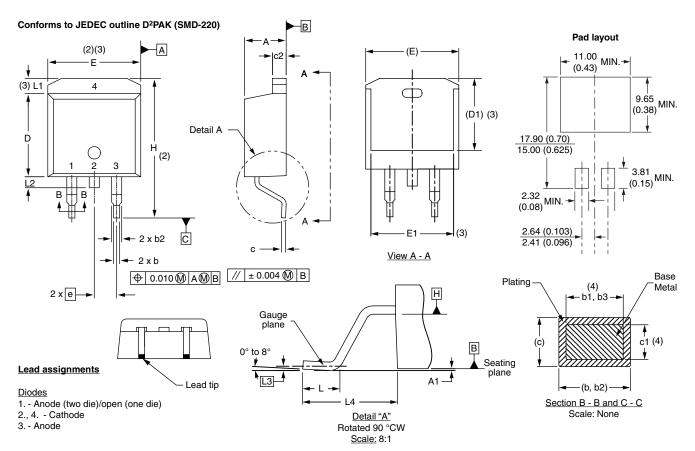
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95014			
Part marking information	www.vishay.com/doc?95008			
Packaging information	www.vishay.com/doc?95032			



Vishay High Power Products

D²PAK, TO-262

DIMENSIONS FOR D²PAK in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIM	ETERS	INC	HES	NOTES
OTMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}\,$ Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch

(7) Outline conforms to JEDEC outline TO-263AB

Vishay High Power Products

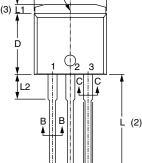
D²PAK, TO-262

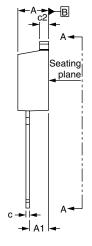


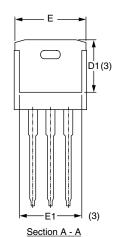
DIMENSIONS FOR TO-262 in millimeters and inches

(Datum A) (2) (3) E A

Modified JEDEC outline TO-262







♦0.010**⋒**|A**⋒**|B

Lead assignments

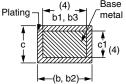


Diodes

-3 x b2 --3 x b

> 1. - Anode (two die)/open (one die) 2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

CVMPOL	MILLIM	MILLIMETERS		INCHES		
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
Е	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54	BSC	0.100) BSC		
L	13.46	14.10	0.530	0.555		
L1	=	1.65	-	0.065	3	
L2	3.56	3.71	0.140	0.146		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline



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